

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

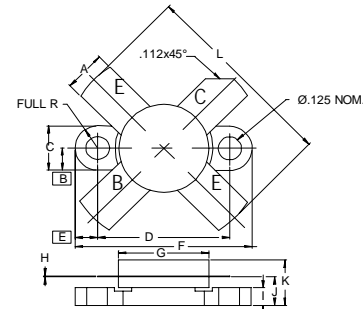
The **ASI MS1000** is a class A silicon NPN planar transistor, designed for SSB communications

FEATURES:

- $P_G = 15$ dB min. at 125 W/30 MHz
- High linear power output
- **IMD** = -30 dBc max. at 125 W_(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CBO}	65 V
V_{CEO}	36 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.65 °C/W

PACKAGE STYLE .500 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K	.280 / 7.11	
L	.980 / 24.89	1.050 / 26.67

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA			35			V
BV_{CES}	$I_C = 100$ mA			65			V
BV_{CBO}	$I_C = 100$ mA			65			
BV_{EBO}	$I_E = 10$ mA			4.0			V
I_{CES}	$V_{CE} = 30$ V					15	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 5.0$ A		10		200	---
C_{ob}	$V_{CB} = 30$ V		$f = 1.0$ MHz	---		285	pF
G_P	$V_{CE} = 28$ V	$P_{IN} = 3.95$ W	$P_{OUT} = 125$ W	15			dB
IMD	$I_{CQ} = 100$ mA	$f = 30.001$ MHz				-30	dBc